

TECHNICAL DATA DATA SHEET 4758, REV. G

HERMETIC SCHOTTKY RECTIFIER Very Low Forward Voltage Drop

Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	60	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form (Single)	60	А
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form (Common Cathode)	60	А
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave (per leg)	860	А
Non-Repetitive Avalanche Energy	Eas	T _J = 25 °C, I _{AS} = 3.0 A, L = 4.4 mH (per leg)	20	mJ
Repetitive Avalanche Current	I _{AR}	I_{AS} decay linearly to 0 in 1 μ s f limited by T_J max V_A =1.5 V_R	3.0	А
Maximum Thermal Resistance (per leg)	Rыс	DC operation	0.7	°C/W
Max. Junction Temperature	ΤJ	-	-65 to +175	°C
Max. Storage Temperature	T _{stg}	-	-65 to +175	°C

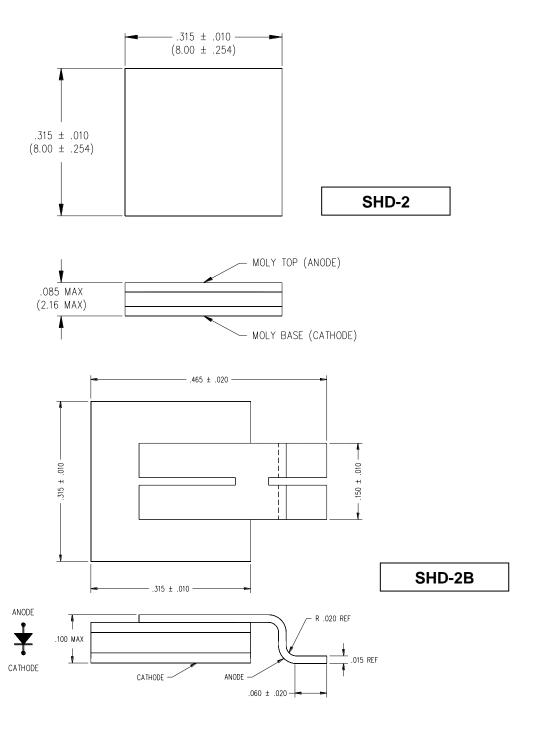
Electrical Characteristics

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V _{F1}	@ 60A, Pulse, T _J = 25 °C	0.70	V
(per leg)	V _{F2}	@ 60A, Pulse, T _J = 125 °C	0.67	V
Max. Reverse Current	I _{R1}	@V _R = 60V, Pulse,	6	mA
		T _J = 25 °C		
(per leg)	I_{R2}	@V _R = 60V, Pulse,	420	mA
		T _J = 125 °C		
Max. Junction Capacitance	Ст	@V _R = 5V, T _C = 25 °C	2400	pF
(per leg)		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV (p-p)}$		

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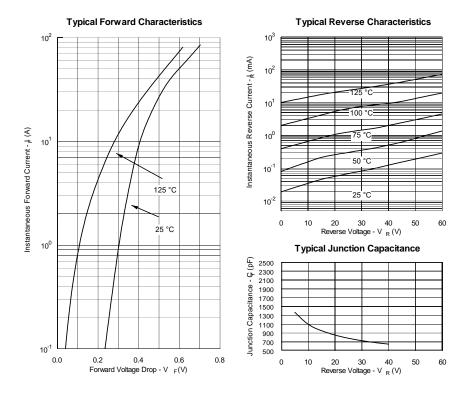
MECHANICAL DIMENSIONS*: In Inches / mm

*Dimensions shown are with solder dipping.



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Note: The V_f curves shown are for the unpackaged die only.



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